

SOT23 NPN SILICON PLANAR SMALL SIGNAL TRANSISTORS

BCW60

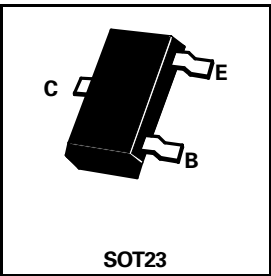
ISSUE 2 – AUGUST 1995

PARTMARKING DETAILS

BCW60A – AA	BCW60AR – CR
BCW60B – AB	BCW60BR – DR
BCW60C – AC	BCW60CR – AR
BCW60D – AD	BCW60DR – BR

COMPLEMENTARY TYPE

BCW61



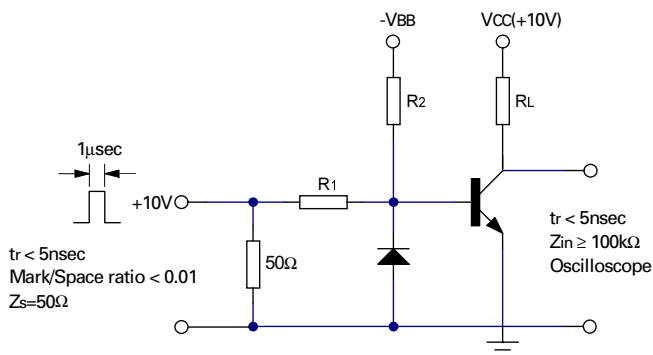
ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	32	V
Collector-Emitter Voltage	V_{CEO}	32	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	200	mA
Base Current	I_B	50	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{TOT}	330	mW
Operating and Storage Temperature Range	tj:tstg	-55 to +150	$^{\circ}C$

FOUR TERMINAL NETWORK DATA ($I_C=2mA$, $V_{CE}=5V$, $f=1kHz$)

	h_{FE} Group A			h_{FE} Group B			h_{FE} Group C			h_{FE} Group D			
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
h_{11e}	1.6	2.7	4.5	2.5	3.6	6.0	3.2	4.5	8.5	4.5	7.5	12	$k\Omega$
h_{12e}		1.5			2			2			3		10^{-4}
h_{21e}		200			260			330			520		
h_{22e}		18	30		24	50		30	60		50	100	μS

SWITCHING CIRCUIT



BCW60

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	32			V	$I_C=2\text{mA}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_{EBO}=1\mu\text{A}$
Collector-Emitter Cut-off Current	I_{CES}			20 20	nA μA	$V_{CES}=32\text{V}$ $V_{CES}=32\text{V}, T_{amb}=150^{\circ}\text{C}$
Emitter-Base Cut-Off Current	I_{EBO}			20	nA	$V_{EBO}=4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.12 0.20	0.35 0.55	V V	$I_C=10\text{mA}, I_B=0.25\text{mA}$ $I_C=50\text{mA}, I_B=1.25\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.60 0.70	0.70 0.83	0.85 1.05	V V	$I_C=10\text{mA}, I_B=0.25\text{mA}$ $I_C=50\text{mA}, I_B=1.25\text{mA}$
Base - Emitter Voltage	V_{BE}	0.55	0.52 0.65 0.78	0.75	V V V	$I_C=10\mu\text{A}, V_{CE}=5\text{V}$ $I_C=2\text{mA}, V_{CE}=5\text{V}$ $I_C=50\text{mA}, V_{CE}=1\text{V}$
Static BCW60A Forward Current Ratio	h_{FE}	120 50	78 170	220		$I_C=10\mu\text{A}, V_{CE}=5\text{V}$ $I_C=2\text{mA}, V_{CE}=5\text{V}$ $I_C=50\text{mA}, V_{CE}=1\text{V}$
BCW60B			20 180 70			145 250
BCW60C		40 250 90	220 350	460		$I_C=10\mu\text{A}, V_{CE}=5\text{V}$ $I_C=2\text{mA}, V_{CE}=5\text{V}$ $I_C=50\text{mA}, V_{CE}=1\text{V}$
BCW60D		100 380 100	300 500	630		$I_C=10\mu\text{A}, V_{CE}=5\text{V}$ $I_C=2\text{mA}, V_{CE}=5\text{V}$ $I_C=50\text{mA}, V_{CE}=1\text{V}$
Transition Frequency	f_T	125	250		MHz	$I_C=10\text{mA}, V_{CE}=5\text{V}$ $f=100\text{MHz}$
Emitter-Base Capacitance	C_{ebo}		8		pF	$V_{EBO}=0.5\text{V}, f=1\text{MHz}$
Collector-Base Capacitance	C_{cbo}			4.5	pF	$V_{CBO}=10\text{V}, f=1\text{MHz}$
Noise Figure	N		2	6	dB	$I_C=0.2\text{mA}, V_{CE}=5\text{V}$ $R_G=2\text{K}\Omega, f=1\text{KH}$ $\Delta f=200\text{Hz}$
Switching times: Delay Time Rise Time Turn-on Time Storage Time Fall Time Turn-Off Time	t_d t_r t_{on} t_s t_f t_{off}		35 50 85 400 80 480	150 800	ns ns ns ns ns ns	$I_{C1}:I_{B1}:-I_{B2}=10:1:1\text{mA}$ $R_1=5\text{K}\Omega, R_2=5\text{K}\Omega$ $V_{BB}=3.6\text{V}, R_L=990\Omega$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle
 Spice parameter data is available upon request for this device